# Switch-mode NPN Silicon **Power Transistors**

The BUX85G is designed for high voltage, high speed power switching applications like converters, inverters, switching regulators, motor control systems.

### Features

• These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO(sus)</sub>	450	Vdc
Collector–Emitter Voltage	V <sub>CES</sub>	1000	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	2	Adc
Collector Current – Peak (Note 1)	I <sub>CM</sub>	3.0	Adc
Base Current – Continuous	Ι <sub>Β</sub>	0.75	Adc
Base Current – Peak (Note 1)	I <sub>BM</sub>	1.0	Adc
Reverse Base Current – Peak	I <sub>BM</sub>	1	Adc
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above $25^{\circ}C$	P <sub>D</sub>	50 0.4	W ₩/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq$  10%.

### THERMAL CHARACTERISTICS

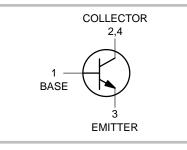
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	ΤL	275	°C

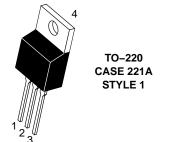


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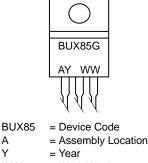
www.onsemi.com

### 2.0 AMPERES **POWER TRANSISTOR NPN SILICON** 450 VOLTS, 50 WATTS





**MARKING DIAGRAM** 



ww = Work Week

А

Y

= Pb-Free Package G

### **ORDERING INFORMATION**

Device	Package	Shipping
BUX85G	TO–220 (Pb–Free)	50 Units / Rail

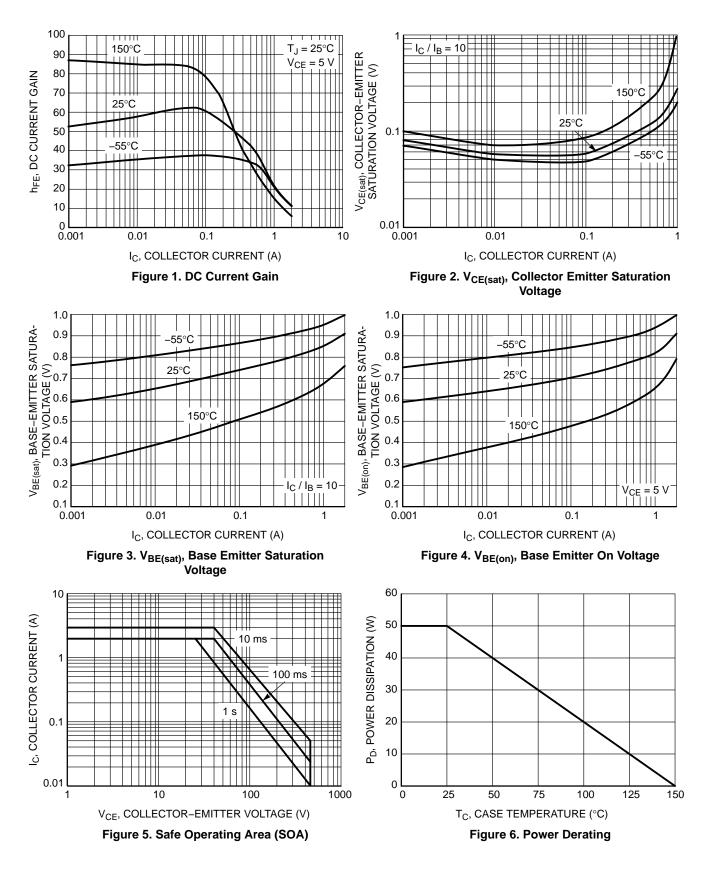
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = $25^{\circ}$ C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERIST	TCS (Note 2)	·				
Collector–Emitter Sus (I <sub>C</sub> = 100 mAdc, (L	staining Voltage = 25 mH) See Figure 1	V <sub>CEO(sus)</sub>	450	-	-	Vdc
Collector Cutoff Current ( $V_{CES}$ = Rated Value) ( $V_{CES}$ = Rated Value, $T_C$ = 125°C)		ICES			0.2 1.5	mAdc
Emitter Cutoff Current (V <sub>EB</sub> = 5 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	_	1	mAdc
ON CHARACTERISTI	<b>CS</b> (Note 2)	·				
DC Current Gain ( $I_C = 0.1 \text{ Adc}, V_{CE} = 5 \text{ V}$ )		h <sub>FE</sub>	30	50	-	-
Collector–Emitter Sat ( $I_C = 0.3 \text{ Adc}, I_B = 3$ ( $I_C = 1 \text{ Adc}, I_B = 20$	30 mAdc)	V <sub>CE(sat)</sub>			0.8 1	Vdc
Base–Emitter Saturation Voltage ( $I_C = 1$ Adc, $I_B = 0.2$ Adc)		V <sub>BE(sat)</sub>	_	-	1.1	Vdc
DYNAMIC CHARACT	ERISTICS		I.			
	$\label{eq:current-Gain-Bandwidth Product} (I_C = 500 \text{ mAdc}, V_{CE} = 1 \text{ 0 Vdc}, \text{ f} = 1 \text{ MHz})$		4	_	-	MHz
SWITCHING CHARAC	CTERISTICS	·				
Turn-on Time	V <sub>CC</sub> = 250 Vdc, I <sub>C</sub> = 1 A	t <sub>on</sub>	-	0.3	0.5	μs
Storage Time	$I_{B1} = 0.2 \text{ A}, I_{B2} = 0.4 \text{ A}$	t <sub>s</sub>	-	2	3.5	μs
Fall Time	See Figure 2	t <sub>f</sub>	-	0.3	-	μs
Fall Time	Same above cond. at $T_C = 95^{\circ}C$	t <sub>f</sub>	_	-	1.4	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test:  $PW = 300 \ \mu$ s, Duty Cycle  $\leq 2\%$ .

### **TYPICAL CHARACTERISTICS**



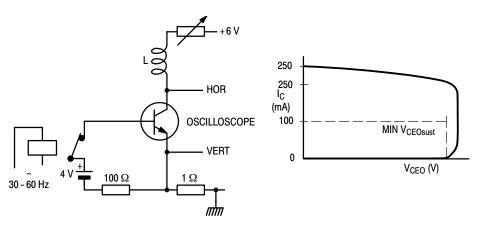
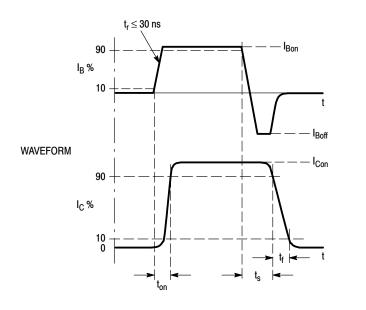
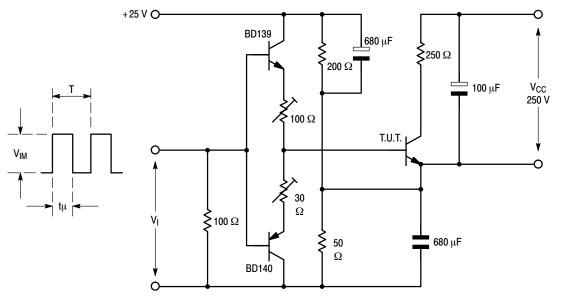
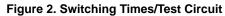


Figure 1. Test Circuit for V<sub>CEOsust</sub>

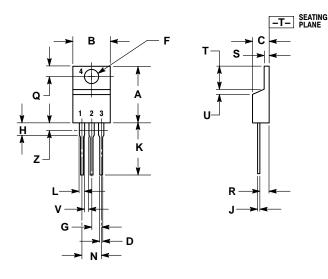






#### PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH** 



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

3

DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Η	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
۷	0.045		1.15		
Ζ		0.080		2.04	

STYLE 1: BASE PIN 1. 2. COLLECTOR FMITTER 3 COLLECTOR

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